

Yoon Jang Chung

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/5165450/publications.pdf>

Version: 2024-02-01

39
papers

741
citations

516710

16
h-index

552781

26
g-index

39
all docs

39
docs citations

39
times ranked

997
citing authors

#	ARTICLE	IF	CITATIONS
1	Growth of p-Type Tin(II) Monoxide Thin Films by Atomic Layer Deposition from Bis(1-dimethylamino-2-methyl-2-propoxy)tin and H ₂ O. Chemistry of Materials, 2014, 26, 6088-6091.	6.7	76
2	Ultra-high-quality two-dimensional electron systems. Nature Materials, 2021, 20, 632-637.	27.5	76
3	Correlation of the change in transfer characteristics with the interfacial trap densities of amorphous In ⁺ Ga ⁺ Zn ⁺ O thin film transistors under light illumination. Applied Physics Letters, 2011, 98, .	3.3	59
4	Vertically integrated submicron amorphous-In ₂ Ga ₂ ZnO ₇ thin film transistor using a low temperature process. Applied Physics Letters, 2012, 100, 203510.	3.3	34
5	Performance Variation According to Device Structure and the Source/Drain Metal Electrode of a-IGZO TFTs. IEEE Transactions on Electron Devices, 2012, 59, 3357-3363.	3.0	34
6	Observation of spontaneous ferromagnetism in a two-dimensional electron system. Proceedings of the National Academy of Sciences of the United States of America, 2020, 117, 32244-32250.	7.1	28
7	Synthesis of nitrogen doped graphite oxide and its electrochemical properties. Current Applied Physics, 2014, 14, 82-86.	2.4	27
8	Effects of substrate conductivity on cell morphogenesis and proliferation using tailored, atomic layer deposition-grown ZnO thin films. Scientific Reports, 2015, 5, 9974.	3.3	26
9	The Impact of Carbon Concentration on the Crystalline Phase and Dielectric Constant of Atomic Layer Deposited HfO ₂ Films on Ge Substrate. ECS Journal of Solid State Science and Technology, 2012, 1, N33-N37.	1.8	25
10	A Simple Method for Cleaning Graphene Surfaces with an Electrostatic Force. Advanced Materials, 2014, 26, 637-644.	21.0	25
11	Indium tin oxide/InGaZnO bilayer stacks for enhanced mobility and optical stability in amorphous oxide thin film transistors. Applied Physics Letters, 2014, 105, .	3.3	24
12	A study on the influence of local doping in atomic layer deposited Al:ZnO thin film transistors. Journal of Materials Chemistry C, 2014, 2, 9274-9282.	5.5	21
13	The charge trapping characteristics of Si ₃ N ₄ and Al ₂ O ₃ layers on amorphous-indium-gallium-zinc oxide thin films for memory application. Applied Physics Letters, 2012, 100, 183503.	3.3	20
14	Study on the defects in metal-organic chemical vapor deposited zinc tin oxide thin films using negative bias illumination stability analysis. Journal of Materials Chemistry C, 2013, 1, 6695.	5.5	18
15	The Electrical Properties of Asymmetric Schottky Contact Thin-Film Transistors with Amorphous-In ₂ Ga ₂ ZnO ₇ . IEEE Transactions on Electron Devices, 2013, 60, 1128-1135.	3.0	18
16	Working principles of doping-well structures for high-mobility two-dimensional electron systems. Physical Review Materials, 2020, 4, .	2.4	18
17	The effects of device geometry on the negative bias temperature instability of Hf-In-Zn-O thin film transistors under light illumination. Applied Physics Letters, 2011, 98, .	3.3	16
18	Properties of Atomic Layer Deposited HfO ₂ Films on Ge Substrates Depending on Process Temperatures. Journal of the Electrochemical Society, 2012, 159, G33-G39.	2.9	16

#	ARTICLE	IF	CITATIONS
19	Design rules for modulation-doped AlAs quantum wells. Physical Review Materials, 2017, 1, .	2.4	16
20	Multivalley two-dimensional electron system in an AlAs quantum well with mobility exceeding 2×10^8 cm ² /Vs. Physical Review Letters, 2017, 118, 076802.	2.4	16
21	Improvement in the negative bias illumination temperature stress instability of InGaZnO thin film transistors using an Al ₂ O ₃ buffer layer. Physica Status Solidi - Rapid Research Letters, 2011, 5, 178-180.	2.4	15
22	Study on the Existence of Abnormal Hysteresis in Hf-In-Zn-O Thin Film Transistors under Illumination. Electrochemical and Solid-State Letters, 2011, 14, H300.	2.2	15
23	Spectroscopic Investigation on the Origin of Photoinduced Carrier Generation in Semiconducting InGaO and InGaZnO Films. Journal of Physical Chemistry C, 2010, 114, 11962-11964.	3.1	14
24	Surface segregation and the Al problem in GaAs quantum wells. Physical Review Materials, 2018, 2, .	2.4	14
25	Direct Observation of Hole Current in Amorphous Oxide Semiconductors under Illumination. Electrochemical and Solid-State Letters, 2011, 14, G35.	2.2	12
26	Reduction of Charge Trapping in HfO ₂ Film on Ge Substrates by Atomic Layer Deposition of Various Passivating Interfacial Layers. IEEE Transactions on Electron Devices, 2012, 59, 2350-2356.	3.0	12
27	Record-quality GaAs two-dimensional hole systems. Physical Review Materials, 2022, 6, .	2.4	12
28	Drawing Circuits with Carbon Nanotubes: Scratch-Induced Graphoepitaxial Growth of Carbon Nanotubes on Amorphous Silicon Oxide Substrates. Scientific Reports, 2014, 4, 5289.	3.3	11
29	Resistive Switching in TiO ₂ Thin Films Using the Semiconducting In-Ga-Zn-O Electrode. IEEE Electron Device Letters, 2012, 33, 582-584.	3.9	10
30	Optical modeling and experimental verification of light induced phenomena in In-Ga-Zn-O thin film transistors with varying gate insulator thickness. Journal of Applied Physics, 2012, 111, 024511.	2.5	8
31	Correlated States of 2D Electrons near the Landau Level Filling $\nu = 1/2$. Physical Review Letters, 2022, 128, 026802.	7.8	8
32	Spatial Mapping of Local Density Variations in Two-dimensional Electron Systems Using Scanning Photoluminescence. Nano Letters, 2019, 19, 1908-1913.	9.1	7
33	Fabrication of free-standing Al ₂ O ₃ nanosheets for high mobility flexible graphene field effect transistors. Journal of Materials Chemistry C, 2014, 2, 4759.	5.5	4
34	Nano-glass frit for inkjet printed front side metallization of silicon solar cells prepared by sol-gel process. Physica Status Solidi - Rapid Research Letters, 2015, 9, 293-296.	2.4	4
35	Trimethylsilylcyclopentadienyl tris(dimethylamino)zirconium as a single-source metal precursor for the atomic layer deposition of ZrSi _{1-x} O ₄ . Thin Solid Films, 2014, 564, 140-145.	1.8	2
36	Amorphous Oxide Semiconductor Memory Using High-k Charge Trap Layer. ECS Transactions, 2010, 33, 375-380.	0.5	0

#	ARTICLE	IF	CITATIONS
37	The Effect of Light Illumination on Transfer Curve and Stability of Amorphous Hf-In-ZnO Thin Film Transistors. ECS Transactions, 2010, 33, 319-324.	0.5	0
38	The Effect of Illumination on the Negative Bias Temperature Instability in Zinc Tin Oxide Thin Film Transistors. ECS Transactions, 2010, 33, 325-330.	0.5	0
39	Heterostructure design to achieve high quality, high density GaAs 2D electron system with g-factor tending to zero. Applied Physics Letters, 2020, 117, 022102.	3.3	0